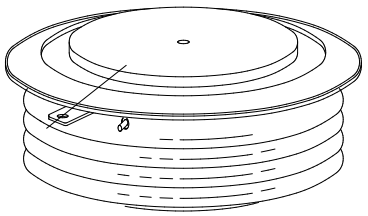
****

T12C



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP2100/40	4000	4000	4100
KP2100/42	4200	4200	4300
KP2100/45	4500	4500	4600

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 120 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/ s

Peak gate power dissipation	P_{GM}		20	W	
Average gate power dissipation	$P_{G(AV)}$		4	W	
Gate-trigger current	I_{GT}		200	mA	V_D =12 V;R_L = 3 ohms;T_j = +25 °C
Gate- trigger voltage	V_{GT}	0.7	2.6	V	V_D = 12 V;R_L = 3 ohms;T_j = +25 °C
Peak